

7300 PIXELS \times 3 COLOR CCD LINEAR IMAGE SENSOR

The μ PD3728 is a high-speed and high sensitive color CCD (Charge Coupled Device) linear image sensor which changes optical images to electrical signal and has the function of color separation.

The μ PD3728 has 3 rows of 7300 pixels, and it is a 2-output/color type CCD sensor with 2 rows/color of charge transfer register, which transfers the photo signal electrons of 7300 pixels separately in odd and even pixels. Therefore, it is suitable for 600 dpi/A3 high-speed color digital copiers and so on.

FEATURES

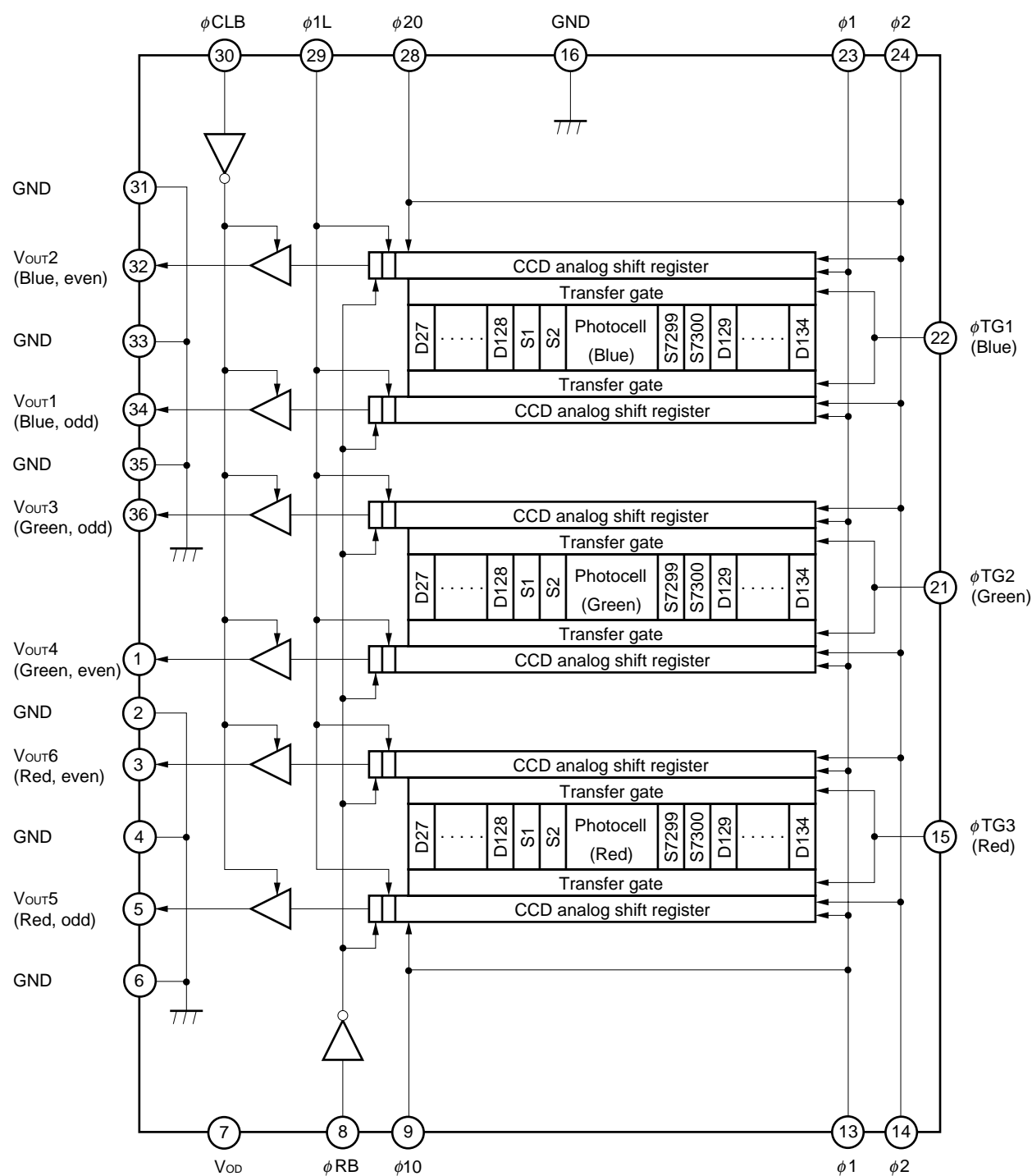
- Valid photocell : 7300 pixels \times 3
- Photocell's pitch : 10 μ m
- Line spacing : 40 μ m (4 lines) Red line-Green line, Green line-Blue line
- Color filter : Primary colors (red, green and blue), pigment filter (with light resistance 10^7 lx \cdot hour)
- Resolution : 24 dot/mm (600 dpi) A3 (297 \times 420 mm) size (shorter side)
- Drive clock level : CMOS output under 5 V operation
- Data rate : 40 MHz MAX. (20 MHz/1 output)
- Output type : 2 outputs in phase/color
- Power supply : +12 V
- On-chip circuits : Reset feed-through level clamp circuits
Voltage amplifiers

ORDERING INFORMATION

Part Number	Package
μ PD3728D	CCD linear image sensor 36-pin ceramic DIP (600 mil)

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Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

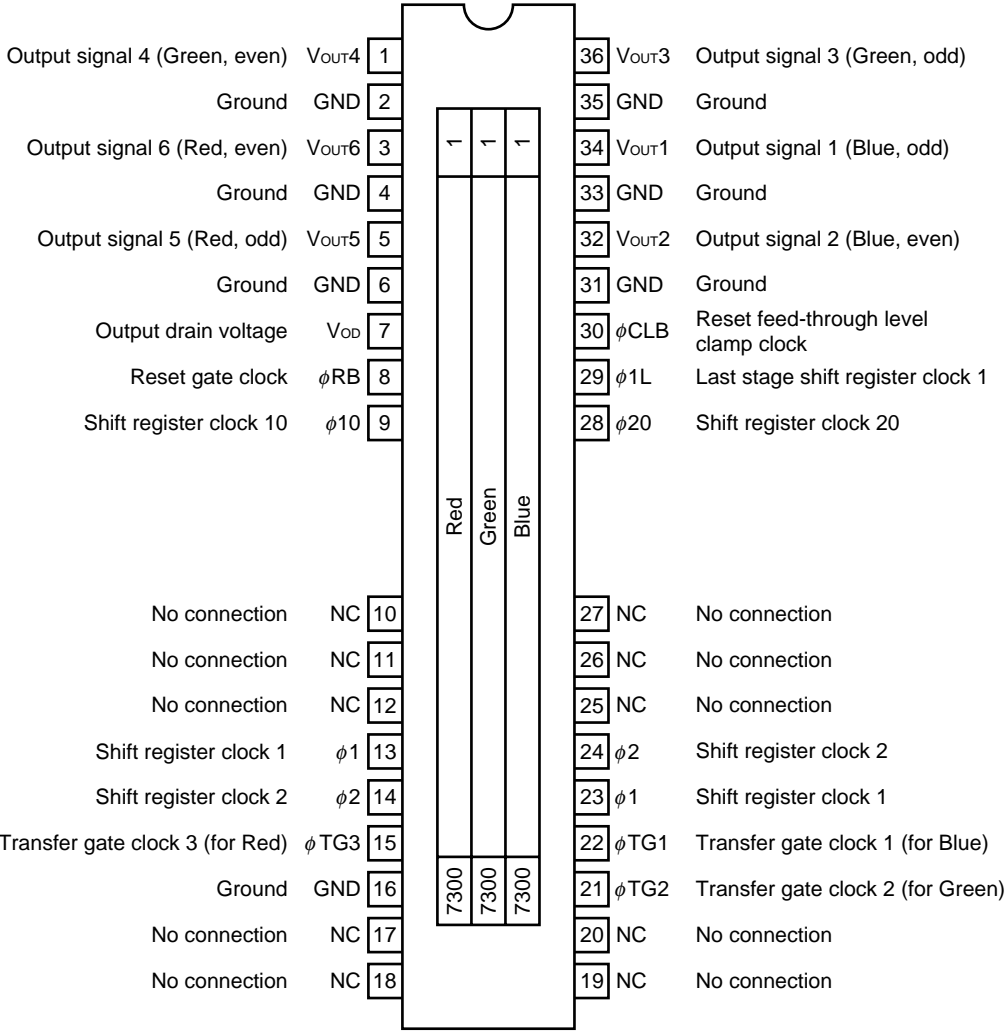
BLOCK DIAGRAM



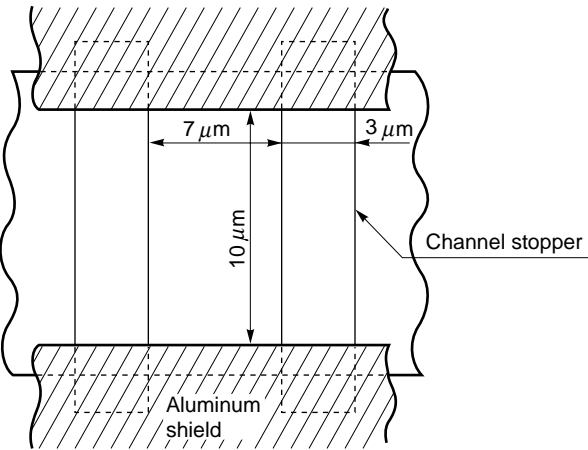
PIN CONFIGURATION (Top View)

CCD linear image sensor 36-pin ceramic DIP (600 mil)

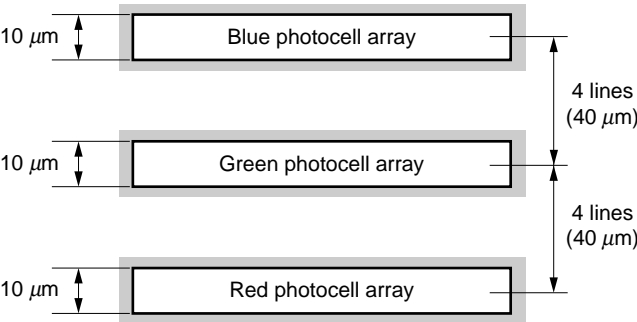
- μPD3728D



PHOTOCELL STRUCTURE DIAGRAM



PHOTOCELL ARRAY STRUCTURE DIAGRAM (Line spacing)



ABSOLUTE MAXIMUM RATINGS ($T_A = +25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	Ratings	Unit
Output drain voltage	V_{OD}	-0.3 to +15	V
Shift register clock voltage	$V_{\phi 1}, V_{\phi 1L}, V_{\phi 10}, V_{\phi 2}, V_{\phi 20}$	-0.3 to +15	V
Reset gate clock voltage	$V_{\phi RB}$	-0.3 to +15	V
Reset feed-through level clamp clock voltage	$V_{\phi CLB}$	-0.3 to +15	V
Transfer gate clock voltage	$V_{\phi TG1}$ to $V_{\phi TG3}$	-0.3 to +15	V
Operating ambient temperature	T_A	-25 to +60	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-40 to +100	$^{\circ}\text{C}$

Caution Exposure to ABSOLUTE MAXIMUM RATINGS for extended periods may affect device reliability; exceeding the ratings could cause permanent damage. The parameters apply independently.

RECOMMENDED OPERATING CONDITIONS ($T_A = +25\text{ }^{\circ}\text{C}$)

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Output drain voltage	V_{OD}	11.4	12.0	12.6	V
Shift register clock high level	$V_{\phi 1H}, V_{\phi 1LH}, V_{\phi 10H}, V_{\phi 2H}, V_{\phi 20H}$	4.5	5.0	5.5	V
Shift register clock low level	$V_{\phi 1L}, V_{\phi 1LL}, V_{\phi 10L}, V_{\phi 2L}, V_{\phi 20L}$	-0.3	0	+0.5	V
Reset gate clock high level	$V_{\phi RBH}$	4.5	5.0	5.5	V
Reset gate clock low level	$V_{\phi RBL}$	-0.3	0	+0.5	V
Reset feed-through level clamp clock high level	$V_{\phi CLBH}$	4.5	5.0	5.5	V
Reset feed-through level clamp clock low level	$V_{\phi CLBL}$	-0.3	0	+0.5	V
Transfer gate clock high level ^{Note}	$V_{\phi TG1H}$ to $V_{\phi TG3H}$	4.5	$V_{\phi 1H}$ ($V_{\phi 10H}$)	$V_{\phi 1H}$ ($V_{\phi 10H}$)	V
Transfer gate clock low level	$V_{\phi TG1L}$ to $V_{\phi TG3L}$	-0.3	0	+0.5	V
Data rate	$2f_{\phi RB}$	—	2	40	MHz

Note When Transfer gate clock high level ($V_{\phi TG1H}$ to $V_{\phi TG3H}$) is higher than Shift register clock high level ($V_{\phi 1H}$ ($V_{\phi 10H}$)), Image lag can increase.

Remark Pin 9 ($\phi 10$) and pin 28 ($\phi 20$) should be open to decrease the influence of input clock noise to output signal waveform, in case of operating at low or middle speed range; data rate under 24 MHz or so.

ELECTRICAL CHARACTERISTICS

($T_A = +25\text{ }^\circ\text{C}$, $V_{OD} = 12\text{ V}$, $f_{\phi RB} = 1\text{ MHz}$, data rate = 2 MHz, storage time = 10 ms,
light source: 3200 K halogen lamp +C-500S (infrared cut filter, $t = 1\text{ mm}$), input signal clock = 5 V_{p-p})

Parameter		Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Saturation voltage		V_{sat}		1.5	2.0	—	V
Saturation exposure	Red	SER			0.35		lx·s
	Green	SEG			0.39		lx·s
	Blue	SEB			0.31		lx·s
Photo response non-uniformity		PRNU	$V_{OUT} = 1\text{ V}$		6	18	%
Average dark signal Note 1		ADS1	Light shielding		1.0	5.0	mV
		ADS2			0.5	5.0	mV
Dark signal non-uniformity Note 1		DSNU1	Light shielding		2.0	5.0	mV
		DSNU2			1.0	5.0	mV
Power consumption		P_W			600	800	mW
Output impedance		Z_O			0.3	0.5	k Ω
Response	Red	R_R		3.9	5.6	7.3	V/lx·s
	Green	R_G		3.6	5.1	6.6	V/lx·s
	Blue	R_B		4.5	6.4	8.3	V/lx·s
Image lag Note 1		IL1	$V_{OUT} = 1\text{ V}$		2.0	5.0	%
		IL2			1.0	5.0	%
Offset level Note 2		V_{OS}		4.0	5.0	6.0	V
Output fall delay time Note 3		t_d	$V_{OUT} = 1\text{ V}$		20		ns
Register imbalance		RI	$V_{OUT} = 1\text{ V}$	0		4.0	%
Total transfer efficiency		TTE	$V_{OUT} = 1\text{ V}$, data rate = 40 MHz	95	98		%
Response peak	Red				630		nm
	Green				540		nm
	Blue				460		nm
Dynamic range Note 1		DR11	$V_{sat}/DSNU1$		1000		times
		DR12	$V_{sat}/DSNU2$		2000		times
		DR21	V_{sat}/σ_{bit1}		2000		times
		DR22	V_{sat}/σ_{bit2}		4000		times
Reset feed-through noise Note 2		RFTN	Light shielding	−500	+200	+500	mV
Random noise Note 1		σ_{bit1}	Light shielding, bit clamp mode ($t_7 = 150\text{ ns}$)	—	1.0	—	mV
		σ_{bit2}		—	0.5	—	mV
		σ_{line1}	Light shielding, line clamp mode ($t_{19} = 3\text{ }\mu\text{s}$)	—	4.0	—	mV
		σ_{line2}		—	2.0	—	mV

Notes 1. ADS1, DSNU1, IL1, DR11, DR21, σ_{bit1} and σ_{line1} show the specification of V_{OUT1} and V_{OUT2} .
ADS2, DSNU2, IL2, DR12, DR22, σ_{bit2} and σ_{line2} show the specification of V_{OUT3} to V_{OUT6} .

2. Refer to **TIMING CHART 2, 5**.

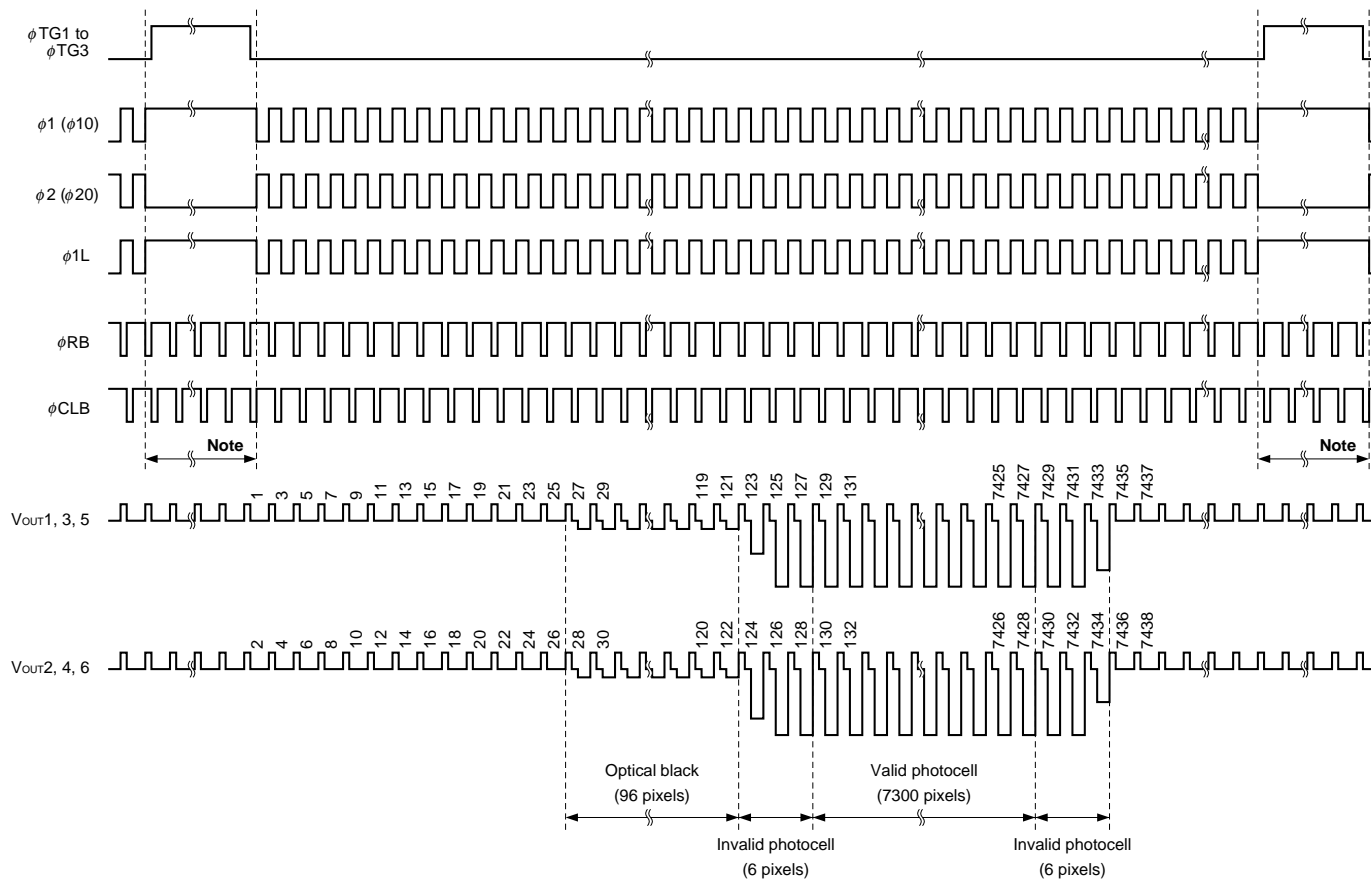
3. When the fall time of ϕ_{1L} (t_2') is the TYP. value (refer to **TIMING CHART 2, 5**).

INPUT PIN CAPACITANCE ($T_A = +25\text{ }^{\circ}\text{C}$, $V_{OD} = 12\text{ V}$)

Parameter	Symbol	Pin name	Pin No.	MIN.	TYP.	MAX.	Unit
Shift register clock pin capacitance 1	$C_{\phi 1}$	$\phi 1$	13		350	500	pF
			23		350	500	pF
		$\phi 10$	9		350	500	pF
Shift register clock pin capacitance 2	$C_{\phi 2}$	$\phi 2$	14		350	500	pF
			24		350	500	pF
		$\phi 20$	28		350	500	pF
Last stage shift register clock pin capacitance	$C_{\phi L}$	$\phi 1L$	29		10		pF
Reset gate clock pin capacitance	$C_{\phi RB}$	ϕRB	8		10		pF
Reset feed-through level clamp clock pin capacitance	$C_{\phi CLB}$	ϕCLB	30		10		pF
Transfer gate clock pin capacitance	$C_{\phi TG}$	$\phi TG1$	22		100		pF
		$\phi TG2$	21		100		pF
		$\phi TG3$	15		100		pF

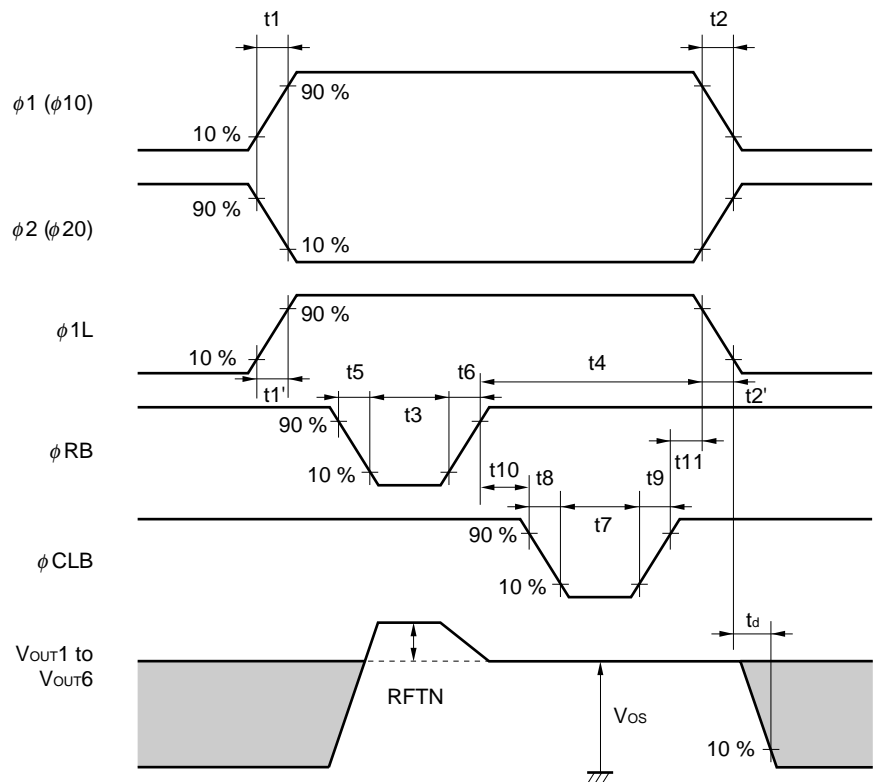
Remark Pins 13, 23 ($\phi 1$) and pin 9 ($\phi 10$) are connected each other inside of the device.
Pins 14, 24 ($\phi 2$) and pin 28 ($\phi 20$) are connected each other inside of the device.

TIMING CHART 1 (Bit clamp mode, for each color)



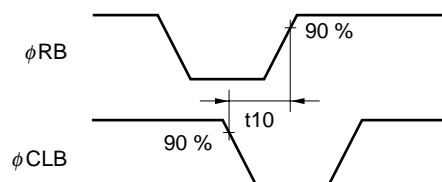
Note Input the ϕ RB and ϕ CLB pulses continuously during this period, too.

TIMING CHART 2 (Bit clamp mode, for each color)

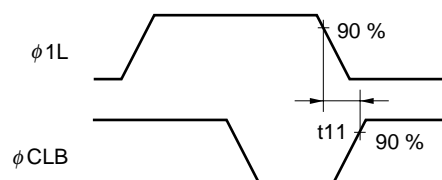


Symbol	MIN.	TYP.	MAX.	Unit
t1, t2	0	50		ns
t1', t2'	0	5		ns
t3	20	50		ns
t4	5	200	—	ns
t5, t6	0	20		ns
t7	20	150		ns
t8, t9	0	20		ns
t10	−10 ^{Note 1}	+50	—	ns
t11	−5 ^{Note 2}	+50		ns

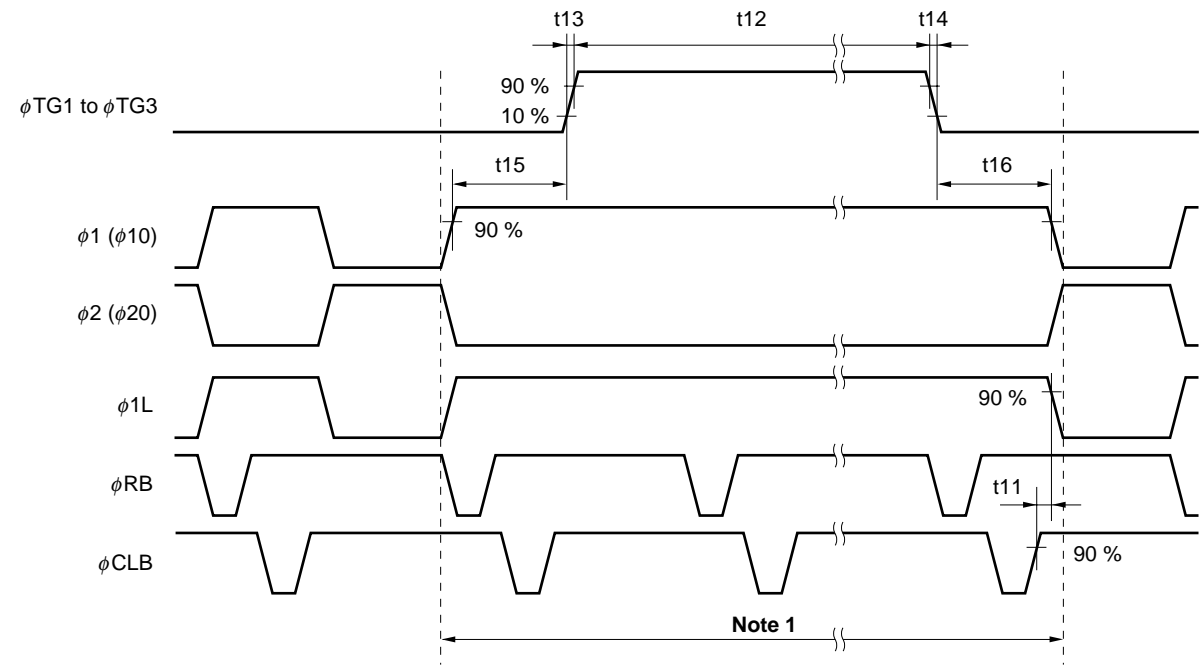
Notes 1. MIN. of t10 shows that the ϕ RB and ϕ CLB overlap each other.



2. MIN. of t11 shows that the ϕ 1L and ϕ CLB overlap each other.

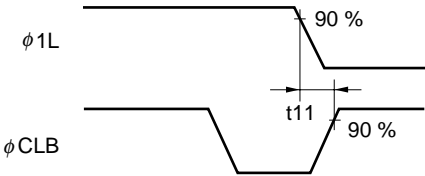


TIMING CHART 3 (Bit clamp mode, for each color)

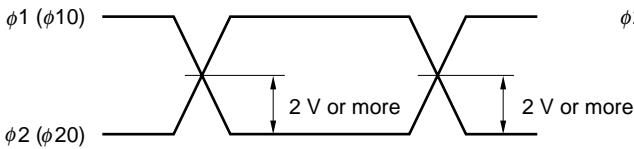


Symbol	MIN.	TYP.	MAX.	Unit
t11	-5 Note 2	+50		ns
t12	3000	10000		ns
t13, t14	0	50		ns
t15, t16	900	1000		ns

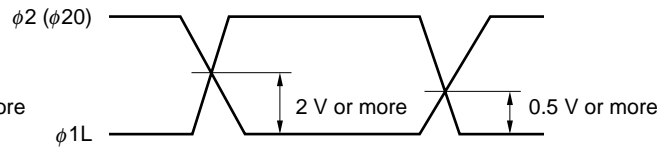
- Notes**
1. Input the ϕ_{RB} and ϕ_{CLB} pulses continuously during this period, too.
 2. MIN. of t11 shows that the ϕ_{1L} and ϕ_{CLB} overlap each other.



ϕ1 (ϕ10), ϕ2 (ϕ20) cross points

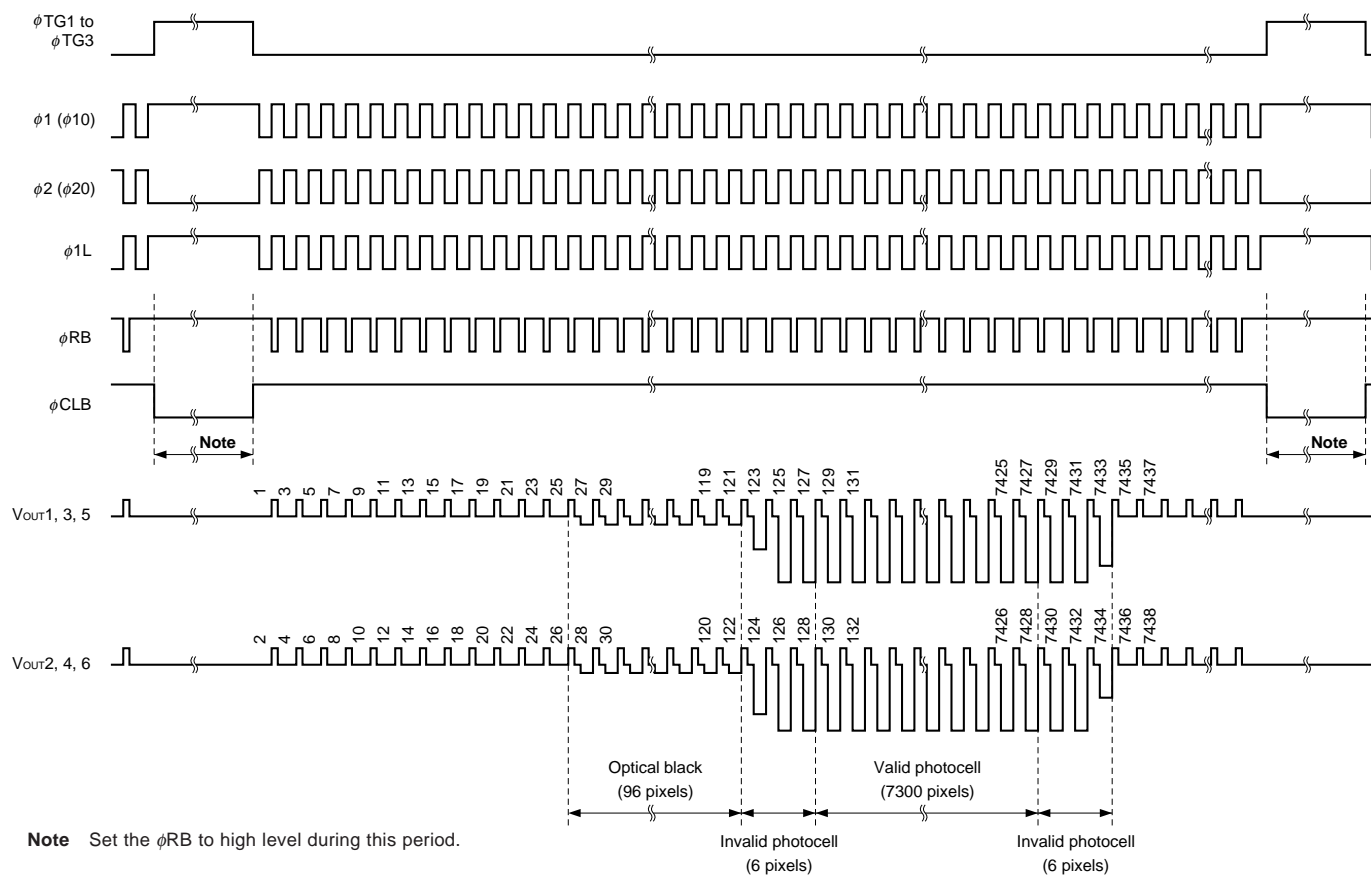


ϕ1L, ϕ2 (ϕ20) cross points



Remark Adjust cross points (ϕ_1 (ϕ_{10}), ϕ_2 (ϕ_{20})) and (ϕ_{1L} , ϕ_2 (ϕ_{20})) with input resistance of each pin.

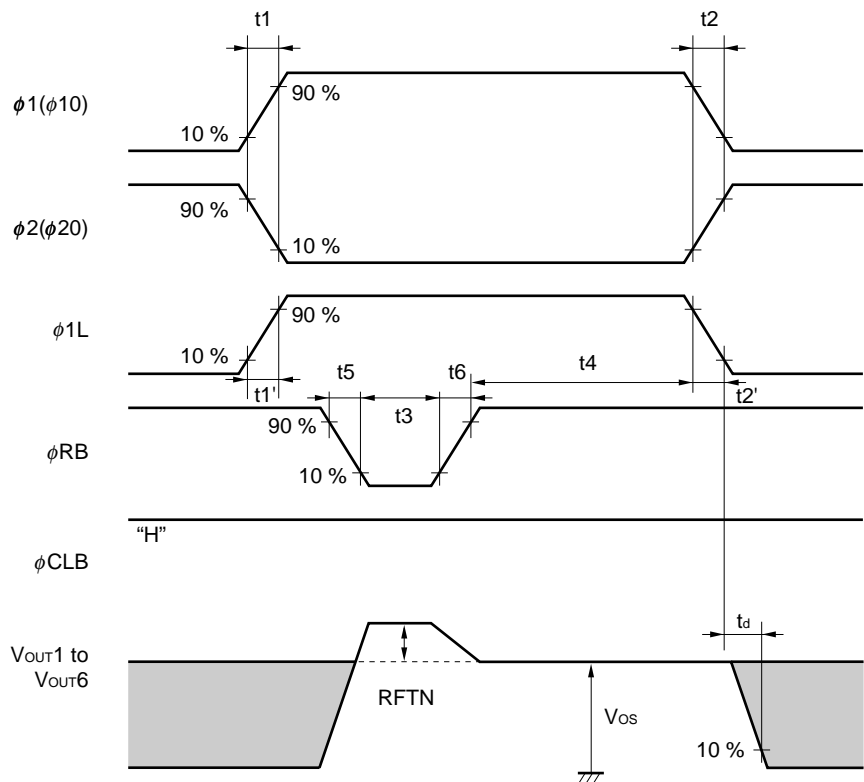
TIMING CHART 4 (Line clamp mode, for each color)



Note Set the ϕ_{RB} to high level during this period.

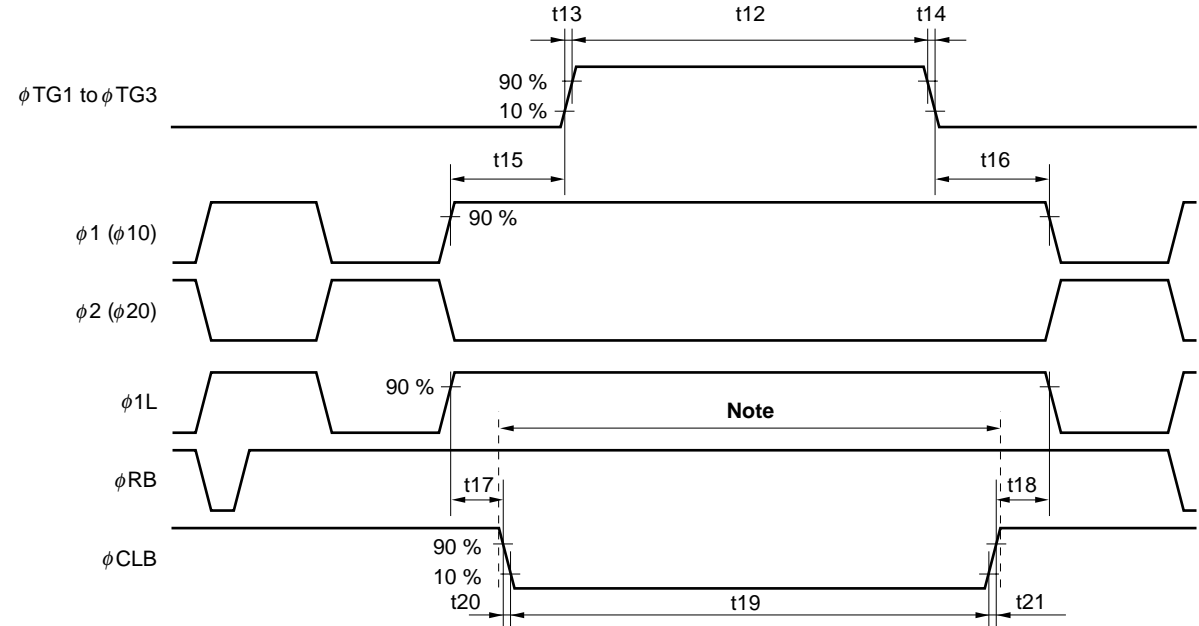
Remark Inverse pulse of the ϕ_{TG1} to ϕ_{TG3} can be used as ϕ_{CLB} .

TIMING CHART 5 (Line clamp mode, for each color)



Symbol	MIN.	TYP.	MAX.	Unit
t1, t2	0	50		ns
t1', t2'	0	5		ns
t3	20	50		ns
t4	5	200	—	ns
t5, t6	0	20		ns

TIMING CHART 6 (Line clamp mode, for each color)

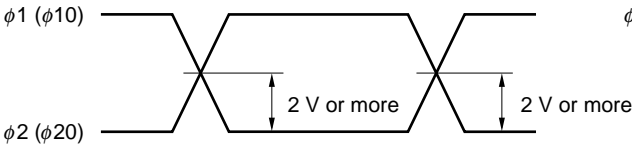


Symbol	MIN.	TYP.	MAX.	Unit
t12	3000	10000		ns
t13, t14	0	50		ns
t15, t16	900	1000		ns
t17, t18	100	1000		ns
t19	200	t12		ns
t20, t21	0	20		ns

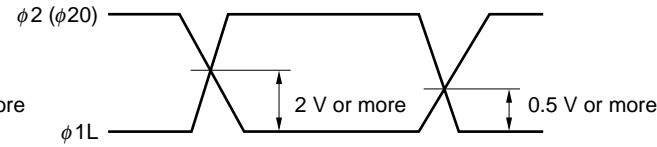
Note Set the ϕRB to high level during this period.

Remark Inverse pulse of the $\phi TG1$ to $\phi TG3$ can be used as ϕCLB .

$\phi 1$ ($\phi 10$), $\phi 2$ ($\phi 20$) cross points



$\phi 1L$, $\phi 2$ ($\phi 20$) cross points



Remark Adjust cross points ($\phi 1$ ($\phi 10$), $\phi 2$ ($\phi 20$)) and ($\phi 1L$, $\phi 2$ ($\phi 20$)) with input resistance of each pin.

DEFINITIONS OF CHARACTERISTIC ITEMS

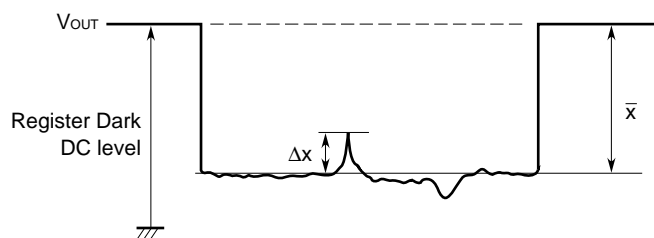
1. Saturation voltage: V_{sat}
Output signal voltage at which the response linearity is lost.
2. Saturation exposure: SE
Product of intensity of illumination (lx) and storage time (s) when saturation of output voltage occurs.
3. Photo response non-uniformity: PRNU
The output signal non-uniformity of all the valid pixels when the photosensitive surface is applied with the light of uniform illumination. This is calculated by the following formula.

$$PRNU (\%) = \frac{\Delta x}{\bar{x}} \times 100$$

Δx : maximum of $|x_j - \bar{x}|$

$$\bar{x} = \frac{\sum_{j=1}^{7300} x_j}{7300}$$

x_j : Output voltage of valid pixel number j



4. Average dark signal: ADS
Average output signal voltage of all the valid pixels at light shielding. This is calculated by the following formula.

$$ADS (mV) = \frac{\sum_{j=1}^{7300} d_j}{7300}$$

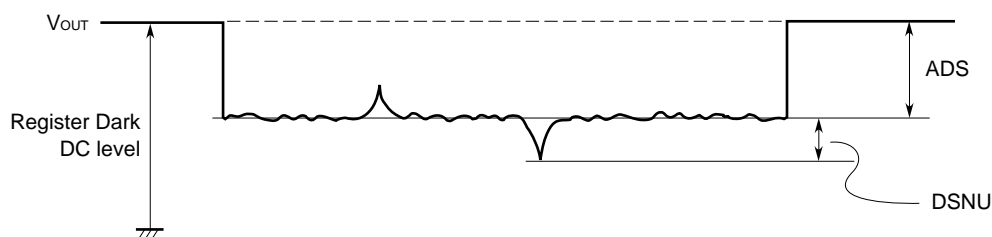
d_j : Dark signal of valid pixel number j

5. Dark signal non-uniformity: DSNU

Absolute maximum of the difference between ADS and voltage of the highest or lowest output pixel of all the valid pixels at light shielding. This is calculated by the following formula.

DSNU (mV) : maximum of $|d_j - \text{ADS}|_{j=1 \text{ to } 7300}$

d_j : Dark signal of valid pixel number j



6. Output impedance: Z_o

Impedance of the output pins viewed from outside.

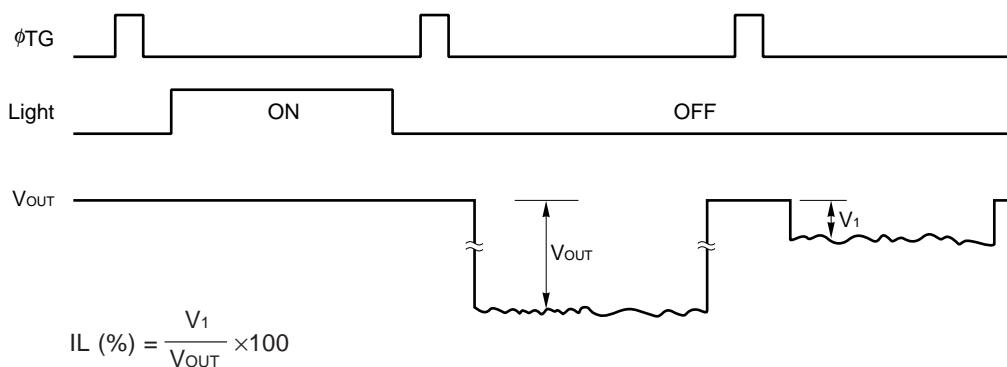
7. Response: R

Output voltage divided by exposure (Ix.s).

Note that the response varies with a light source (spectral characteristic).

8. Image lag: IL

The rate between the last output voltage and the next one after read out the data of a line.



9. Register imbalance: RI

The rate of the difference between the averages of the output voltage of Odd and Even pixels, against the average output voltage of all the valid pixels.

$$RI (\%) = \frac{\frac{2}{n} \left| \sum_{j=1}^{\frac{n}{2}} (V_{2j-1} - V_{2j}) \right|}{\frac{1}{n} \sum_{j=1}^n V_j} \times 100$$

n : Number of valid pixels

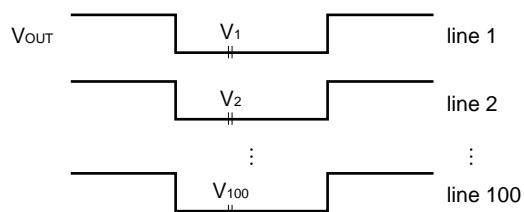
V_j : Output voltage of each pixel

10. Random noise: σ

Random noise σ is defined as the standard deviation of a valid pixel output signal with 100 times (=100 lines) data sampling at dark (light shielding).

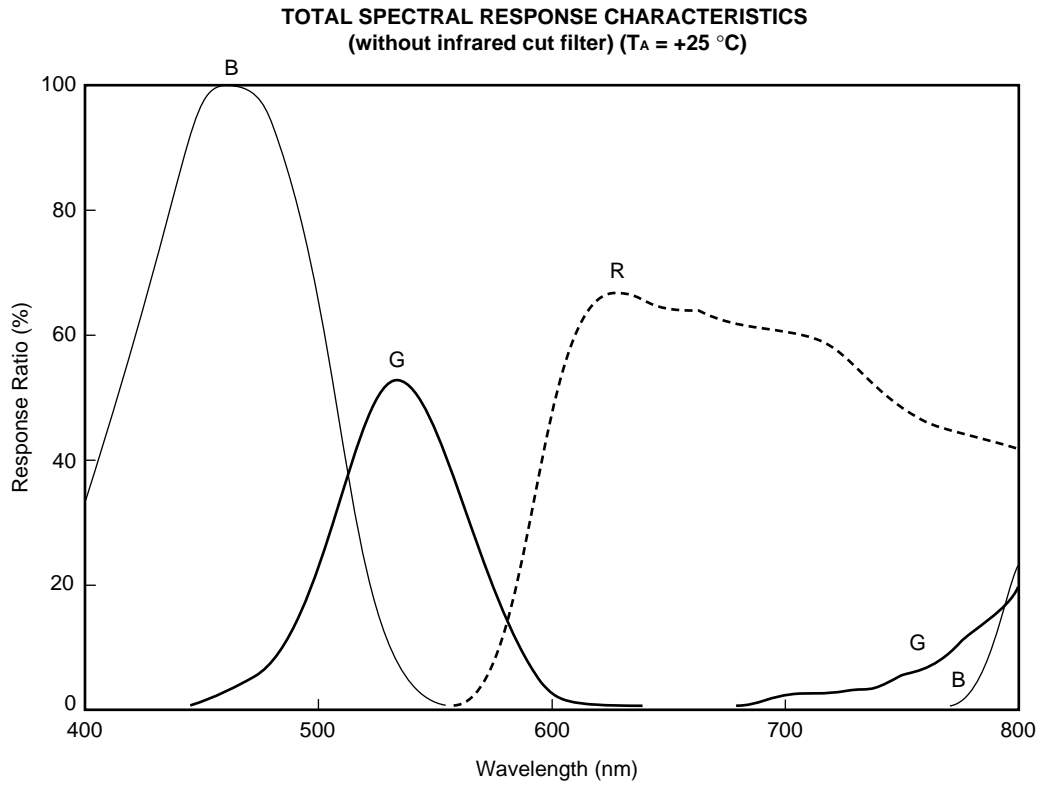
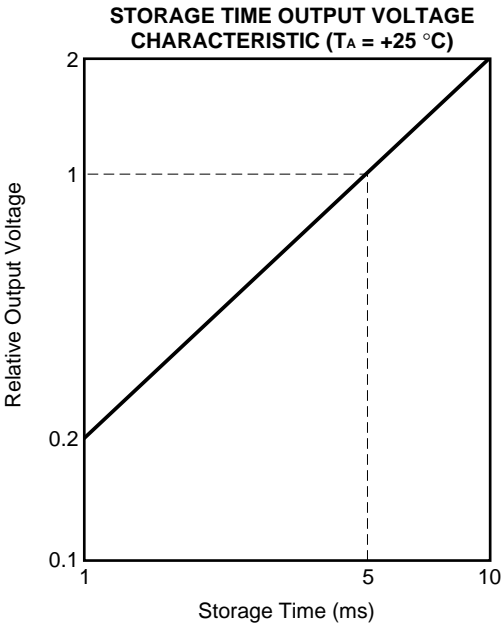
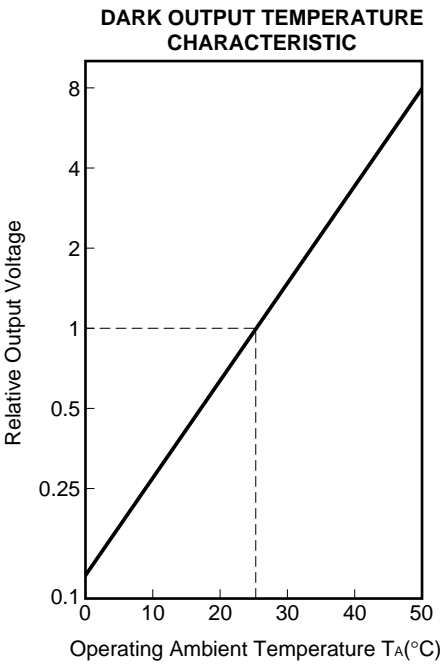
$$\sigma \text{ (mV)} = \sqrt{\frac{\sum_{i=1}^{100} (V_i - \bar{V})^2}{100}}, \quad \bar{V} = \frac{1}{100} \sum_{i=1}^{100} V_i$$

V_i: A valid pixel output signal among all of the valid pixels for each color

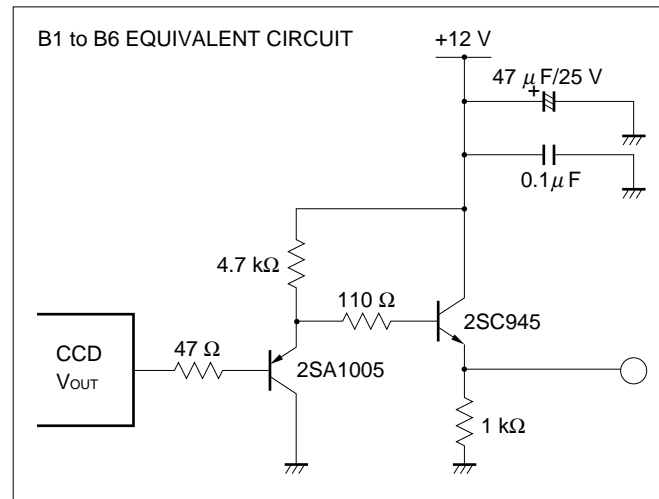


This is measured by the DC level sampling of only the signal level, not by CDS (Correlated Double Sampling).

STANDARD CHARACTERISTIC CURVES (Nominal)



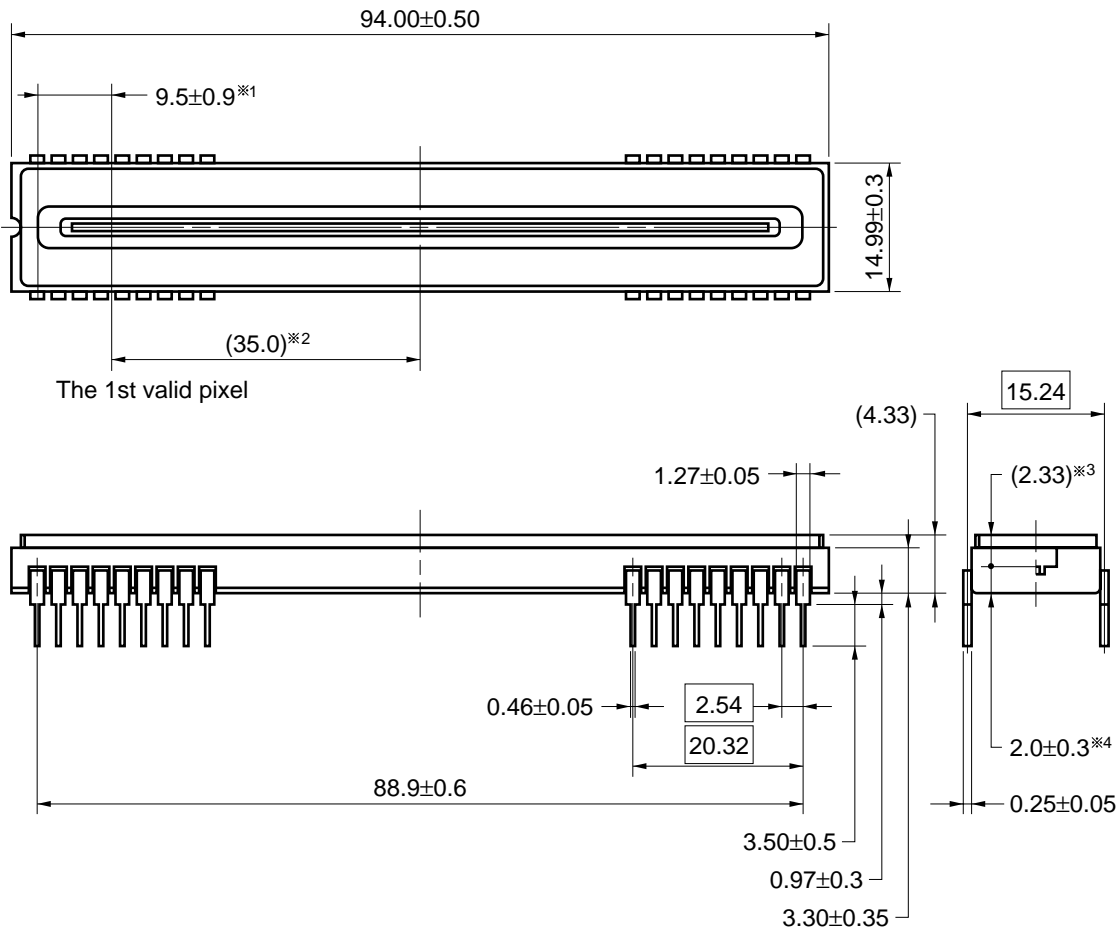
- Downloaded from Elcodis.com electronic components distributor



PACKAGE DRAWING

CCD LINEAR IMAGE SENSOR 36-PIN CERAMIC DIP (600mil)

(Unit : mm)



Name	Dimensions	Refractive index
Glass cap	$93.0 \times 13.6 \times 1.0$	1.5

- ※ 1 The 1st valid pixel ←→ The center of the pin1
※ 2 The 1st valid pixel ←→ The center of the package (Reference)
※ 3 The surface of the chip ←→ The top of the glass cap (Reference)
※ 4 The bottom of the package ←→ The surface of the chip

36D-1CCD-PKG1-1

NOTES ON THE USE OF THE PACKAGE

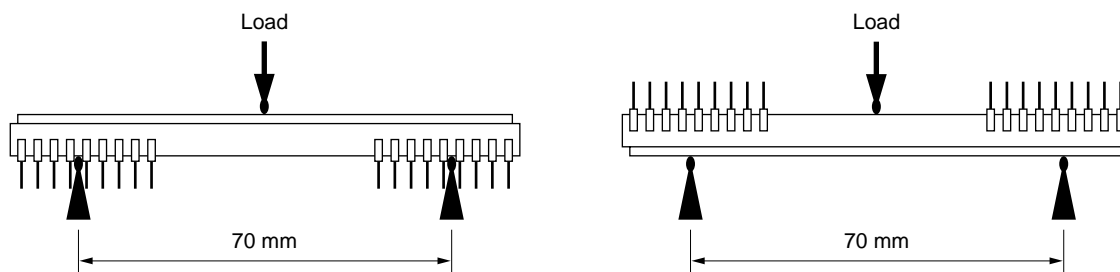
The application of an excessive load to the package may cause the package to warp or break, or cause chips to come off internally. Particular care should be taken when mounting the package on the circuit board.

When mounting the package, use a circuit board which will not subject the package to bending stress, or use a socket.

For this product, the reference value for the three-point bending strength^{Note} is 30 kg. Avoid imposing a load, however, on the inside portion as viewed from the face on which the window (glass) is bonded to the package body (ceramic).

Note Three-point bending strength test

Distance between supports: 70 mm, Support R: R 2 mm, Loading rate: 0.5 mm / min.



[MEMO]

NOTES FOR CMOS DEVICES

① PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note:

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

② HANDLING OF UNUSED INPUT PINS FOR CMOS

Note:

No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to V_{DD} or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

③ STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note:

Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

[MEMO]

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Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots

Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)

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M7 98.8